

## **KSE350**

## **High Voltage General Purpose Applications**

- High Collector-Emitter Breakdown Voltage
- Suitable for Transformer
- Complement to KSE340



## **PNP Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	- 300	V
V <sub>CEO</sub>	Collector-Emitter Voltage	- 300	V
V <sub>EBO</sub>	Emitter-Base Voltage	- 5	V
I <sub>C</sub>	Collector Current	- 500	mA
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	20	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C

### **Electrical Characteristics** $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = -1 \text{ mA}, I_B = 0$	-300		V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -300V, I_{E} = 0$		-100	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE} = -3V, I_{C} = 0$		-100	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE} = -10V, I_{C} = -50mA$	30	240	

# **Typical Characteristics**

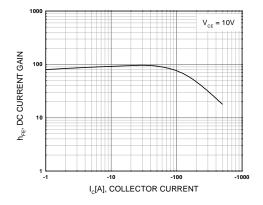


Figure 1. DC current Gain

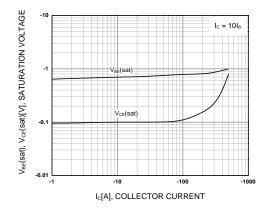


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

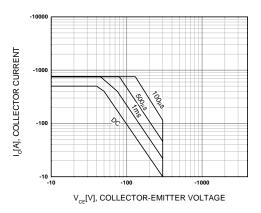


Figure 3. Safe Operating Area

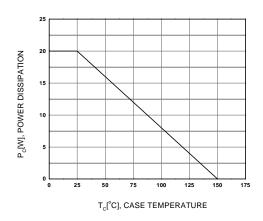
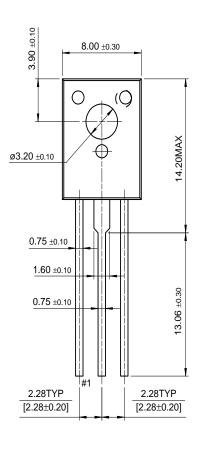
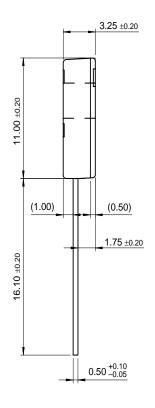


Figure 4. Power Derating

## **Package Demensions**

TO-126







Dimensions in Millimeters

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